

IN THE CLAIMS:

Amend claims 1 and 16 as indicated below:

Q2 1. (Amended) A high frequency semiconductor device comprising:
a semiconductor substrate;
at least one active element formed on said semiconductor substrate;
a ground plate connected to a ground potential, said ground plate being provided above said active element;
at least one insulating interlayer;
a plurality of line conductors provided above said ground plate, with said at least one insulating interlayer provided therebetween;
at least one terminal for connecting to the exterior; and
a shield plate provided above a highest layer of the plurality of line conductors, with said at least one insulating interlayer provided therebetween, said shield plate being connected to the ground potential and covering the plurality of line conductors.

Q3 16. (Amended) A high frequency semiconductor device according to Claim 14, wherein said terminal is a flip chip bonding electrode.

Add new claims 21-24 as follows:

Q4 21. A high frequency semiconductor device comprising:
a semiconductor substrate;

a ground plate connected to the ground potential;
at least one insulating interlayer;
a line conductor provided above said ground plate, with said at least one insulating interlayer provided therebetween;
at least one terminal for connecting to the exterior; and
a shield plate provided above the highest layer of the line conductor, with said at least one insulating interlayer provided therebetween, said shield plate being connected to the ground potential;
wherein said semiconductor substrate is divided into an element-arranged area in which semiconductor elements are formed and an outer area around said element-arranged area in which at least one terminal is provided; and
said shield plate selectively covers said element-arranged area.

22. A high frequency semiconductor device comprising:
a semiconductor substrate;
a ground plate connected to the ground potential;
at least one insulating interlayer;
a line conductor provided above said ground plate, with said at least one insulating interlayer provided therebetween;
at least one terminal for connecting to the exterior;

a shield plate provided above the highest layer of the line conductor, with said at least one insulating interlayer provided therebetween, said shield plate being connected to the ground potential;

said semiconductor substrate is divided into an element-arranged area in which semiconductor elements are formed and an outer area around said element-arranged area in which at least one terminal is provided;

said shield plate selectively covers said element-arranged area;

a plurality of throughholes formed in the periphery of said shield plate so as to surround an inner area excluding the periphery, the throughholes reaching said ground plate; and

internal conductors provided in the throughholes, said internal conductors connecting said shield plate and said ground plate;

wherein said at least one terminal and said element-arranged area are made in conduction by an area in which the throughholes are not provided.

23. A high frequency semiconductor device comprising:

a semiconductor substrate;

a ground plate connected to the ground potential;

at least one insulating interlayer;

a line conductor provided above said ground plate, with said at least one insulating interlayer provided therebetween;

at least one terminal for connecting to the exterior; and

a shield plate provided above the highest layer of the line conductor, with said at least one insulating interlayer provided therebetween, said shield plate being connected to the ground potential;

wherein said terminal is a patch antenna.

24. A high frequency semiconductor device comprising:

a semiconductor substrate;

a ground plate connected to the ground potential;

at least one insulating interlayer;

a line conductor provided above said ground plate, with said at least one insulating interlayer provided therebetween;

at least one terminal for connecting to the exterior; and

a shield plate provided above the highest layer of the line conductor, with said at least one insulating interlayer provided therebetween, said shield plate being connected to the ground potential;

wherein said at least one insulating interlayer is made of one of polyimide and benzocyclobutene.